

	Hits	Search Text	DBs
2	0	((substrate or wafer) same (gate near16 (structure or second or pluralit\$4 or multiple)) same liner same spacer same (source near12 drain) same (bit near16 line near15 contact near26 plug)) and ((photoresist or resist) near36 (photolithograph\$5 or expos\$4 or irradiat\$4 or lithograph\$4) near28 (develop\$4 or pattern\$4 or etch\$4 or RIE)) and (first same second same liner) and ((first or initial) near26 (conductive or tungsten or polysilicon or polySi or W or metal\$4) near32 (contact or gate))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
3	0	((substrate or wafer) same (gate near16 (structure or second or pluralit\$4 or multiple)) same liner same spacer same (source near12 drain) same (bit near16 line near15 contact near26 plug)) and ((photoresist or resist) near36 (photolithograph\$5 or expos\$4 or irradiat\$4 or lithograph\$4) near28 (develop\$4 or pattern\$4 or etch\$4 or RIE)) and (first same liner) and ((first or initial) near26 (conductive or tungsten or polysilicon or polySi or W or metal\$4) near32 (contact or gate))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
4	0	((substrate or wafer) same (gate near16 (structure or second or pluralit\$4 or multiple)) same liner same spacer same (source near12 drain) same (bit near16 line near15 contact near26 plug)) and ((photoresist or resist) near36 (photolithograph\$5 or expos\$4 or irradiat\$4 or lithograph\$4) near28 (develop\$4 or pattern\$4 or etch\$4 or RIE)) and ((first or initial) near26 (conductive or tungsten or polysilicon or polySi or W or metal\$4) near32 (contact or gate))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
5	65	((substrate or wafer) same (gate near16 (structure or second or pluralit\$4 or multiple))) and (source near22 drain) and ((photoresist or resist) near36 (photolithograph\$5 or expos\$4 or irradiat\$4 or lithograph\$4) near28 (develop\$4 or pattern\$4 or etch\$4 or RIE)) and ((conductive or tungsten or polysilicon or polySi or W or metal\$4) near32 (contact or gate)) and (ILD or (inter near6 layer near8 dielectric)) and liner and spacer	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
6	0	((substrate or wafer) same (gate near16 (structure or second or pluralit\$4 or multiple)) same liner same spacer) and ((substrate or wafer) same (source near12 drain) same (bit near16 line near15 contact near26 plug)) and ((photoresist or resist) near36 (photolithograph\$5 or expos\$4 or irradiat\$4 or lithograph\$4) near28 (develop\$4 or pattern\$4 or etch\$4 or RIE)) and ((first or initial) near26 (conductive or tungsten or polysilicon or polySi or W or metal\$4) near32 (contact or gate))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
7	1	((substrate or wafer) same (gate near16 (structure or second or pluralit\$4 or multiple)) same liner same spacer) and ((substrate or wafer) same (source near12 drain) same (bit near16 line near15 contact)) and ((photoresist or resist) near36 (photolithograph\$5 or expos\$4 or irradiat\$4 or lithograph\$4) near28 (develop\$4 or pattern\$4 or etch\$4 or RIE)) and ((first or initial) near26 (conductive or tungsten or polysilicon or polySi or W or metal\$4) near32 (contact or gate))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
8	1	((substrate or wafer) same (gate near16 (structure or second or pluralit\$4 or multiple)) same liner same spacer) and ((substrate or wafer) same (source near12 drain)) and (bit near16 line near15 contact near16 plug) and ((photoresist or resist) near36 (photolithograph\$5 or expos\$4 or irradiat\$4 or lithograph\$4) near28 (develop\$4 or pattern\$4 or etch\$4 or RIE)) and ((first or initial) near26 (conductive or tungsten or polysilicon or polySi or W or metal\$4) near32 (contact or gate))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
9	0	((substrate or wafer) same (gate near16 (structure or second or pluralit\$4 or multiple)) same liner same spacer) and ((substrate or wafer) same (source near12 drain)) and (bit near16 line near15 contact near16 plug) and ((photoresist or resist) near36 (photolithograph\$5 or expos\$4 or irradiat\$4 or lithograph\$4) near28 (develop\$4 or pattern\$4 or etch\$4 or RIE)) and ((conductive or tungsten or polysilicon or polySi or W or metal\$4) near32 (contact or gate) near36 damascene)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
10	1	((substrate or wafer) same (gate near16 (structure or second or pluralit\$4 or multiple)) same liner same spacer) and ((substrate or wafer) same (source near12 drain)) and (bit near16 line near15 contact near16 plug) and ((photoresist or resist) near36 (photolithograph\$5 or expos\$4 or irradiat\$4 or lithograph\$4) near28 (develop\$4 or pattern\$4 or etch\$4 or RIE)) and ((conductive or tungsten or polysilicon or polySi or W or metal\$4) near32 (contact or gate)) and (ILD or (inter near6 layer near8 dielectric))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
11	1	((substrate or wafer) same (gate near16 (structure or second or pluralit\$4 or multiple)) same liner same spacer) and (source near22 drain) and (bit near15 contact near16 plug) and ((photoresist or resist) near36 (photolithograph\$5 or expos\$4 or irradiat\$4 or lithograph\$4) near28 (develop\$4 or pattern\$4 or etch\$4 or RIE)) and ((conductive or tungsten or polysilicon or polySi or W or metal\$4) near32 (contact or gate)) and (ILD or (inter near6 layer near8 dielectric))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
12	2	((substrate or wafer) same (gate near16 (structure or second or pluralit\$4 or multiple))) and (source near22 drain) and (bit near15 contact near16 plug) and ((photoresist or resist) near36 (photolithograph\$5 or expos\$4 or irradiat\$4 or lithograph\$4) near28 (develop\$4 or pattern\$4 or etch\$4 or RIE)) and ((conductive or tungsten or polysilicon or polySi or W or metal\$4) near32 (contact or gate)) and (ILD or (inter near6 layer near8 dielectric)) and liner and spacer	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
13	34	((substrate or wafer) same (gate near16 (structure or second or pluralit\$4 or multiple))) and (source near22 drain) and ((photoresist or resist) near36 (photolithograph\$5 or expos\$4 or irradiat\$4 or lithograph\$4) near28 (develop\$4 or pattern\$4 or etch\$4 or RIE)) and (first near30 (conductive or tungsten or polysilicon or polySi or W or metal\$4) near32 (contact or gate)) and (ILD or (inter near6 layer near8 dielectric)) and liner and spacer and (planariz\$6 or CMP or (chemical near9 mechanical near9 polish\$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
14	56	((substrate or wafer) same (gate near16 (structure or second or pluralit\$4 or multiple))) and (source near22 drain) and ((photoresist or resist) near36 (photolithograph\$5 or expos\$4 or irradiat\$4 or lithograph\$4) near28 (develop\$4 or pattern\$4 or etch\$4 or RIE)) and ((conductive or tungsten or polysilicon or polySi or W or metal\$4) near32 (contact or gate)) and (ILD or (inter near6 layer near8 dielectric)) and liner and spacer and (planariz\$6 or CMP or (chemical near9 mechanical near9 polish\$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
15	22	S14 NOT S13	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
16	42	((substrate or wafer) same (gate near16 (structure or second or pluralit\$4 or multiple))) and (source near22 drain) and ((photoresist or resist) near36 (photolithograph\$5 or expos\$4 or irradiat\$4 or lithograph\$4) near28 (develop\$4 or pattern\$4 or etch\$4 or RIE)) and ((conductive or tungsten or polysilicon or polySi or W or metal\$4) near32 (contact or gate)) and (ILD or (inter near6 layer near8 dielectric)) and liner and spacer and (second near22 (conductive or metal\$4 or tungsten or W or polysilicon or polySi))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
17	34	((substrate or wafer) same (gate near16 (structure or second or pluralit\$4 or multiple))) and (source near22 drain) and ((photoresist or resist) near36 (photolithograph\$5 or expos\$4 or irradiat\$4 or lithograph\$4) near28 (develop\$4 or pattern\$4 or etch\$4 or RIE)) and (first near30 (conductive or tungsten or polysilicon or polySi or W or metal\$4) near32 (contact or gate)) and (ILD or (inter near6 layer near8 dielectric)) and liner and spacer and (planariz\$6 or CMP or (chemical near9 mechanical near9 polish\$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
18	32	S16 NOT S19	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
19	56	((substrate or wafer) same (gate near16 (structure or second or pluralit\$4 or multiple))) and (source near22 drain) and ((photoresist or resist) near36 (photolithograph\$5 or expos\$4 or irradiat\$4 or lithograph\$4) near28 (develop\$4 or pattern\$4 or etch\$4 or RIE)) and ((conductive or tungsten or polysilicon or polySi or W or metal\$4) near32 (contact or gate)) and (ILD or (inter near6 layer near8 dielectric)) and liner and spacer and (planariz\$6 or CMP or (chemical near9 mechanical near9 polish\$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
20	22	S18 NOT S17	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
21	6	((substrate or wafer) same (gate near16 (structure or second or pluralit\$4 or multiple))) and (source near22 drain) and ((photoresist or resist) near36 (photolithograph\$5 or expos\$4 or irradiat\$4 or lithograph\$4) near28 (develop\$4 or pattern\$4 or etch\$4 or RIE)) and ((conductive or tungsten or polysilicon or polySi or W or metal\$4) near32 (contact or gate or (bit near9 line))) and ((ILD or (inter near6 layer near8 dielectric)) near22 second) and ((second or subsequent) near6 liner) and (planariz\$6 or CMP or (chemical near9 mechanical near9 polish\$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
22	5	((substrate or wafer) same (gate near16 (structure or second or pluralit\$4 or multiple))) and (source near22 drain) and ((photoresist or resist) near36 (photolithograph\$5 or expos\$4 or irradiat\$4 or lithograph\$4) near28 (develop\$4 or pattern\$4 or etch\$4 or RIE)) and ((conductive or tungsten or polysilicon or polySi or W or metal\$4) near32 (contact or gate or (bit near9 line))) and ((ILD or (inter near6 layer near8 dielectric)) near22 second) and (liner near12 thickness) and (planariz\$6 or CMP or (chemical near9 mechanical near9 polish\$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
23	23	((substrate or wafer) same (gate near16 (structure or second or pluralit\$4 or multiple))) and (source near22 drain) and ((photoresist or resist) near36 (photolithograph\$5 or expos\$4 or irradiat\$4 or lithograph\$4) near28 (develop\$4 or pattern\$4 or etch\$4 or RIE)) and (conductive or tungsten or polysilicon or polySi or W or metal\$4) and ((ILD or (inter near6 layer near8 dielectric))) and (liner near12 thickness) and (planariz\$6 or CMP or (chemical near9 mechanical near9 polish\$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
24	22	S23 NOT S21	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
25	28	((substrate or wafer) same (gate near16 (first or structure or second or pluralit\$4 or multiple))) and ((source near22 drain) near36 gate) and ((photoresist or resist) near36 (photolithograph\$5 or expos\$4 or irradiat\$4 or lithograph\$4) near28 (develop\$4 or pattern\$4 or etch\$4 or RIE)) and (conductive or tungsten or polysilicon or polySi or W or metal\$4) and ((ILD or (inter near6 layer near8 dielectric) or IMD or (inter near9 metal near9 dielectric)) near25 (second or cap\$4)) and (liner same (planariz\$6 or CMP or (chemical near9 mechanical near9 polish\$4)))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
26	1	("20040198008").PN.	US-PGPUB; USPAT
27	8	((substrate or wafer) same (gate near16 (structure or second or pluralit\$4 or multiple))) and (source near22 drain) and ((photoresist or resist) near36 (photolithograph\$5 or expos\$4 or irradiat\$4 or lithograph\$4) near28 (develop\$4 or pattern\$4 or etch\$4 or RIE) near26 (wet near9 etch\$4) near29 (residu\$4).)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
28	16	((substrate or wafer) same (gate near16 (structure or second or pluralit\$4 or multiple))) and (source near22 drain) and ((photoresist or resist) near36 (photolithograph\$5 or expos\$4 or irradiat\$4 or lithograph\$4) near28 (develop\$4) same (wet near9 etch\$4) same (remov\$4 or strip\$4 or wash\$4 or eliminat\$4) same (residu\$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
29	35	((substrate or wafer) same (gate near16 (conductive or structure or second or pluralit\$4 or multiple))) and (source near22 drain) and ((photoresist or resist) near36 (expos\$4 or irradiat\$4 or illuminat\$4) near28 (develop\$4) same ((wet or liquid or HF) near9 etch\$4) same (remov\$4 or strip\$4 or wash\$4 or eliminat\$4) same (residu\$4 or polymer\$4 or slurr\$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
30	16	((substrate or wafer) same (gate near16 (structure or second or pluralit\$4 or multiple))) and (source near22 drain) and ((photoresist or resist) near36 (photolithograph\$5 or expos\$4 or irradiat\$4 or lithograph\$4) near28 (develop\$4) same (wet near9 etch\$4) same (remov\$4 or strip\$4 or wash\$4 or eliminat\$4) same (residu\$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
31	19	S29 NOT S30	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
32	218	((substrate or wafer) same (gate near16 (conductive or structure or second or pluralit\$4 or multiple))) and (source near22 drain) and ((photoresist or resist) same (wet near9 etch\$4) same (remov\$4 or strip\$4 or wash\$4 or eliminat\$4) same (residu\$4 or polymer\$4 or slurr\$4)) and ((photoresist or resist) near26 (expos\$4 or irradiat\$4 or illuminat\$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB